N-Ch MOSFET

General Description

The WST3406A is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST3406A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

Product Summery

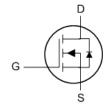
BVDSS	RDSON	ID
30V	18mΩ	7A

Applications

- High Frequency Point-of-Load Synchronous s Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	30	V	
V_{GS}	Gate-Source Voltage	±12	V	
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	7.0	Α	
I _D @T _c =70℃	Continuous Drain Current, V _{GS} @ 10V ¹	6.0	А	
I _{DM}	Pulsed Drain Current ²	25	А	
P _D @T _A =25°C	Total Power Dissipation ³	1	W	
P _D @T _A =70°C	Total Power Dissipation ³	0.64	W	
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$	
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-ambient ¹		125	°C/W
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		95	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		80	°C/W



Electrical Characteristics (T_J=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I _D =1mA		0.025		V/°C
D	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =5A		18	28	mΩ
R _{DS(ON)}		V _{GS} =2.5V , I _D =4A		24	38	
$V_{GS(th)}$	Gate Threshold Voltage	\/ -\/ -250\	0.5	0.8	1.2	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$-V_{GS}=V_{DS}$, $I_D=250uA$		-4.8		mV/℃
	Drain Source Leekege Current	V _{DS} =24V , V _{GS} =0V , T _J =25℃			1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =5A		7		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.5	5	Ω
Qg	Total Gate Charge (4.5V)			6	8.4	
Q _{gs}	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =5A		2.5	3.5	nC
Q_gd	Gate-Drain Charge			2.1	2.9	
T _{d(on)}	Turn-On Delay Time			2.4	4.8	
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω I_{D} =5A		7.8	14	
T _{d(off)}	Turn-Off Delay Time			22	44	ns
T _f	Fall Time			4	8	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		572		
Coss	Output Capacitance			81		pF
C _{rss}	Reverse Transfer Capacitance			65		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V =V =0V Force Current			2	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			25	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_S =1A , T_J =25 $^{\circ}{\mathbb{C}}$			1.2	V
t _{rr}	Reverse Recovery Time			19		nS
Q _{rr}	Reverse Recovery Charge	IF=5A , dI/dt=100A/ μ s , T $_{J}$ =25 $^{\circ}$ C		1.04		nC

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%
- 3.The power dissipation is limited by 150 $^{\circ}\mathrm{C}$ $\,$ junction temperature
- $\textbf{4.The data is theoretically the same as } \textbf{I}_{D} \text{ and } \textbf{I}_{DM} \text{ , in real applications , should be limited by total power dissipation.}$



Typical Characteristics

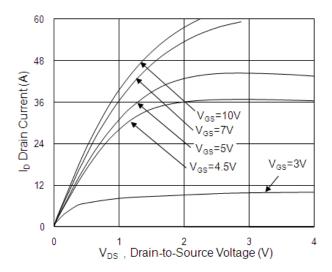


Fig.1 Typical Output Characteristics

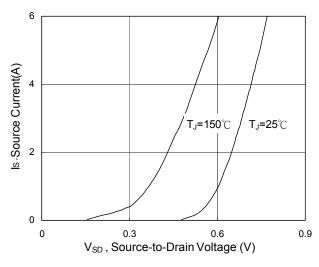


Fig.3 Forward Characteristics Of Reverse

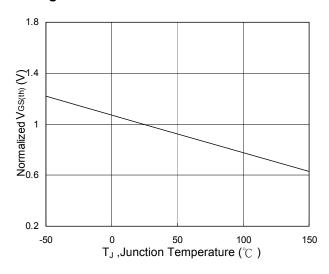


Fig.5 Normalized V_{GS(th)} vs. T_J

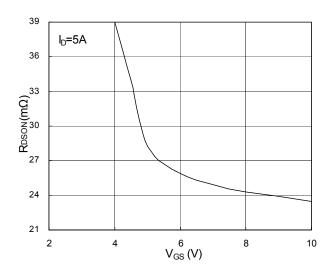


Fig.2 On-Resistance vs. Gate-Source

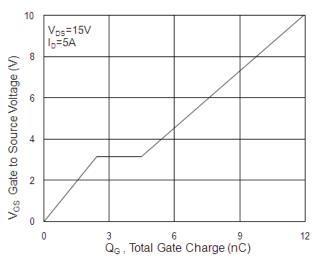


Fig.4 Gate-Charge Characteristics

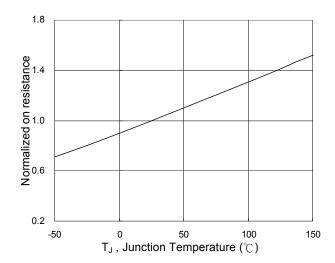
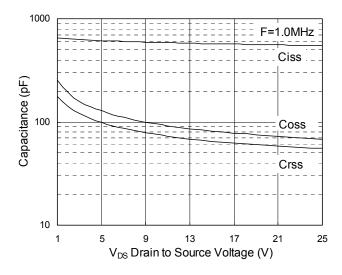


Fig.6 Normalized R_{DSON} vs. T_J





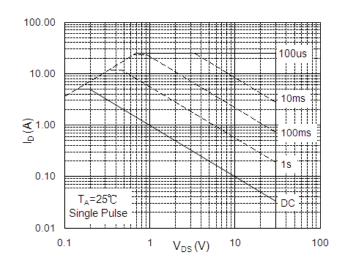


Fig.7 Capacitance

Fig.8 Safe Operating Area

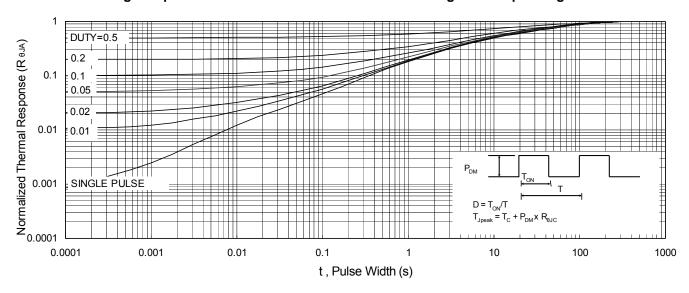


Fig.9 Normalized Maximum Transient Thermal Impedance

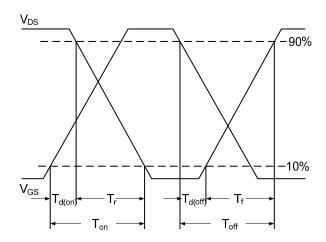


Fig.10 Switching Time Waveform

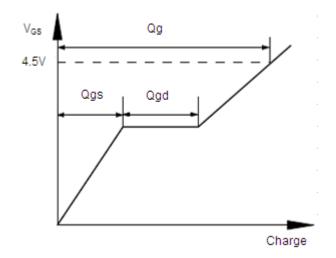


Fig.11 Gate Charge Waveform



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